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		K. McStay et al., "Verti Tephnology Digest of Te							
		J. A. Mandelman et al., IBM Journal of Researc	th and Developm	ent, Vol. 4	6, No. 2/3, March/May	2002, pp. 187 -	208		
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NN H. Akatsu et al., "A highly manufacturable 11 IEEE 2002 Symposium on VLSI Technology I			e 110nm DRAM gy Digest of Tec	technology with 81 chnical Papers	F2 vertical tra	insistor cell for	1Gb and 1	beyond",				
NN		K. McStay et al., "Vertical pass transistor design for sub-100nm DRAM technologies", IEEE 2002 Symposium on VLSI Technology Digest of Technical Papers										
NN	NN J. A. Mandelman et al., "Challenges and future directions for the scaling of dynamic random-access memory (DRAN IBM Journal of Research and Development, Vol. 46, No. 2/3, March/May 2002, pp. 187 - 208							.M)",				
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